# GTMi, Inc.

Solution, Service, Performance, and Commitment

- Your Trusted Partner

Product Data Sheet

Model: GT1214-200L

GaN/SiC High Efficiency Transistor

#### GaN Transistor Product Features

GT1214-200L is an internally pre-matched GaN on SiC HEMT, common source, class AB that capable of providing over 18dB gain, 200 Watts at 3mS pulse width, 30% duty factor across the 1200 to 1400 MHz band. This thermally enhanced transistor is designed for L-band Long Pulse Radar applications. It utilizes gold metallization and eutectic die attach to provide highest reliability and superior ruggedness.

- *High Power* >200W
- *Ultra High Efficiency* >60%
- 3ms, 30%, Long Pulse and High Duty Condition

#### **Market Application**

• L-band Radar For Long Pulse High Duty Cycle Application

#### Case Outline

The following illustrations show the case outline of model GT1214-200L



1.032"x.390"x.135 (include lid)

Case Outline T4

#### Absolute Maximum Ratings

Description	Test Condition	Max	Units
Maximum Power Dissipation	Transistor Dissipation at 25°C	350	W
MVI	Drain Source Voltage $(V_{DSS})$	150	V
Maximum Voltage and Current	Gate Source Voltage $(V_{GS})$	-8 to 0	V
MT	Storage Temperature	-55 to 125	°C
Maximum Temperature	Operating Junction Temperature	200	°C

### RF Specifications, T=25° C

Symbol	Description	Test Condition	Min	Typical	Max	Units
Po	Output Power	Pin=3.2W Freq=1200, 1300, 1400 MHz	200	235		Watts
Gp	Power Gain	Pin=3.2W Freq=1200, 1300, 1400 MHz	18.0	18.7		dB
$n_d$	Drain Efficiency	Pin=3.2W Freq=1200, 1300, 1400 MHz	50	60		%
IRL	Input Return Loss	Pin=3.2W Freq=1200, 1300, 1400 MHz		-9	-7	dB
VSWR-T	Mismatch Tolerance	Pin=3.2W Freq=1300MHz			3:1	
$\theta_{jc}$	Thermal Resistance	3mS, 30% Condition		.70		°C/W
Droop	Pulse Droop	Pin=3.2W Freq=1200, 1300, 1400 MHz		.7	1	dB

• Bias Condition: Vdd=+50V, Idq=80mA average current (Vgs= -2.0 ~ -4.0V typical)

#### DC Characteristics, T=25° C

Symbol	Description	Test Condition	Min	Typical	Max	Units
$I_{D(off)}$	Drain Leakage Current	$V_{GS}$ = -8V, $V_{DD}$ = 150V			9	mA
$I_{G(off)}$	Gate Leakage Current	$V_{GS}$ = -8V, $V_{DD}$ = 0V			3	mA

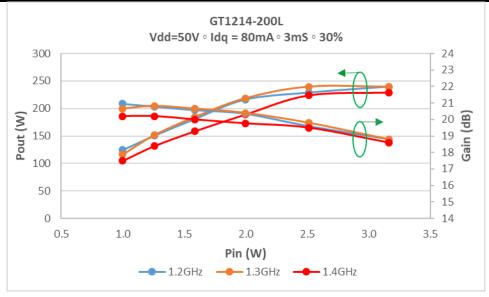
### **Product Classification**

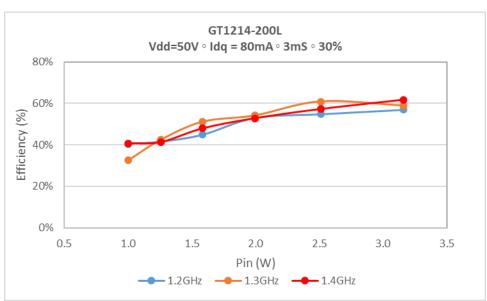
**EAR-99** 

#### **Product Typical Performance**

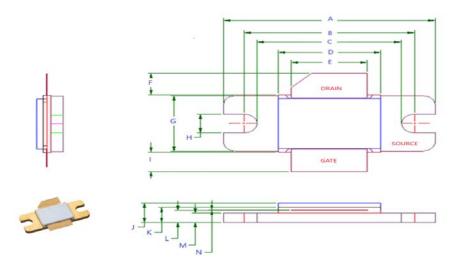
3mS - 30% Pulsing

Frequency (MHz)	Pin (W)	Pout (W)	ld (A)	RTL(dB)	Nd (%)	Gp (dB)	Droop (dB)
1200	3.2	240	2.58	-7.2	57	18.8	0.80
1300	3.2	239	2.50	-8.5	60	18.8	0.65
1400	3.2	230	2.28	-14.0	66	18.6	0.60





## Package Dimensions



Label	Inches	Tolerance	Millimeter	Tolerance
Α	1.03	.010	26.18	.25
В	.830	.004	21.10	.10
С	.700	.004	17.82	.10
D	.498	.002	12.60	.05
E	.370	.002	9.42	.05
F	.152	.002	3.86	.05
G	.385	.004	8.82	.10
Н	.130	.004	3.34	.10
I	.152	.004	3.86	.10
J	.136	.002	3.48	.02
К	.105	.002	2.70	.02
L	.086	.002	2.20	.02
M	.065	.002	1.68	.02
N	.004	.001	0.12	.05

#### Test Circuit Information

(Contact GTMi for Details)

The information contained in the document is PROPRIETARY AND CONFIDENTIAL information of GTMi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of GTMi If the recipient of this document has entered into a disclosure agreement with GTMi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of GTMi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by GTMi in writing signed by an officer of GTMi.

GTMi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with life-support or other mission-critical equipment or applications. GTMi assumes no liability whatsoever, and GTMi disclaims any express or implied warranty, relating to sale and/or use of GTMi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. The product is subject to other terms and conditions which can be located on the Web at http://www.microsemi.com/legal/tnc.asp.

#### Revision History

Revision Level / Date	Para. Affected	Description
Rev 1 / 08-01-2020	•	Initial Preliminary Release